

MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM3J351R

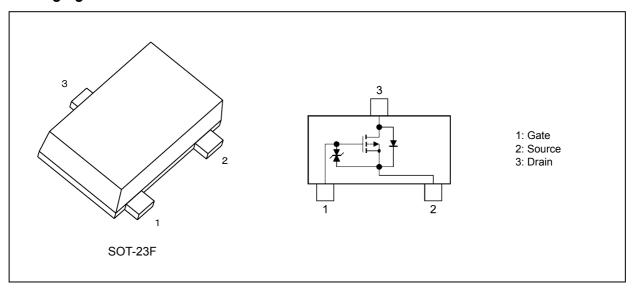
#### 1. Applications

· Power Management Switches

#### 2. Features

- (1) AEC-Q101 qualified (Please see the orderable part number list)
- (2) 4 V drive
- (3) Low drain-source on-resistance
  - :  $R_{DS(ON)} = 107 \text{ m}\Omega \text{ (typ.) } (V_{GS} = -10 \text{ V})$
  - $R_{DS(ON)} = 122 \text{ m}\Omega \text{ (typ.) } (V_{GS} = -4.5 \text{ V})$
  - $R_{\rm DS(ON)} = 129 \ {\rm m}\Omega \ ({\rm typ.}) \ (V_{\rm GS} = -4.0 \ {\rm V})$

### 3. Packaging and Internal Circuit



### 4. Orderable part number

Orderable part number	AEC-Q101		Note			
SSM3J351R,LF	_		General Use			
SSM3J351R,LXGF	YES	(Note 1)	Unintended Use	(Note 1)		
SSM3J351R,LXHF	YES		Automotive Use			

Note 1: For more information, please contact our sales or use the inquiry form on our website.

Start of commercial production



### 5. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	-60	V
Gate-source voltage	,		$V_{GSS}$	-20/+10	
Drain current (DC)		(Note 1)	I <sub>D</sub>	-3.5	Α
Drain current (pulsed)		(Note 1), (Note 2)	I <sub>DP</sub>	-14	
Power dissipation	,	(Note 3)	$P_{D}$	1	W
Power dissipation	(t ≤ 10 s)	(Note 3)	$P_{D}$	2	
Single-pulse avalanche energy		(Note 4)	E <sub>AS</sub>	8.9	mJ
Avalanche current			I <sub>AR</sub>	3.5	Α
Channel temperature			T <sub>ch</sub>	150	℃
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW)  $\leq$  1 ms, duty  $\leq$  1 %
- Note 3: Device mounted on a 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm<sup>2</sup>)
- Note 4:  $V_{DD}$  = 25 V,  $T_{ch}$  = 25 °C (Initial state), L = 1 mH,  $R_G$  = 25  $\Omega$

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 6. Electrical Characteristics

### 6.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

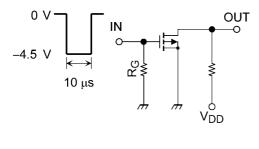
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = -16 \text{ V}/+10 \text{ V}$	_	_	±10	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V	_	_	-10	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 0 V	-60	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 10 V	-50	_	_	
Gate threshold voltage		V <sub>th</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA	-0.8	_	-2.0	
Drain-source on-resistance	(Note 2)	R <sub>DS(ON)</sub>	I <sub>D</sub> = -1.0 A, V <sub>GS</sub> = -4.0 V	_	129	184	mΩ
			I <sub>D</sub> = -1.0 A, V <sub>GS</sub> = -4.5 V	_	122	164	
			I <sub>D</sub> = -1.0 A, V <sub>GS</sub> = -10 V	_	107	134	
Forward transfer admittance	(Note 2)	Y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1.0 A	_	6.4	_	S

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

### 6.2. Dynamic Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V,	-	660	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	50		
Output capacitance	C <sub>oss</sub>		_	70	_	
Switching time (turn-on time)	t <sub>on</sub>	$V_{DD}$ = -30 V, $I_{D}$ = -1.0 A, $V_{GS}$ = 0 to -4.5 V, $R_{G}$ = 10 $\Omega$ ,	_	32		ns
Switching time (turn-off time)	t <sub>off</sub>	Duty $\leq$ 1 %, $V_{IN}$ : $t_r$ , $t_f$ < 5 ns, Common source, See Chapter 6.3.		100		

#### 6.3. Switching Time Test Circuit



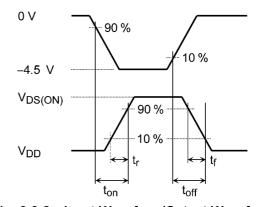


Fig. 6.3.1 Switching Time Test Circuit

Fig. 6.3.2 Input Waveform/Output Waveform

### 6.4. Gate Charge Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} = -48 \text{ V}, I_{D} = -3.5 \text{ A},$	_	15.1	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	V <sub>GS</sub> = -10 V	_	0.6	_	
Gate-drain charge	$Q_{gd}$		_	3		

Note 2: Pulse measurement.

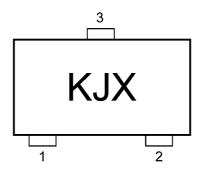


### 6.5. Source-Drain Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage (	(Note 1)	$V_{DSF}$	I <sub>D</sub> = 3.5 A, V <sub>GS</sub> = 0 V	_	0.85	1.2	V

Note 1: Pulse measurement.

### 7. Marking





#### 8. Characteristics Curves (Note)

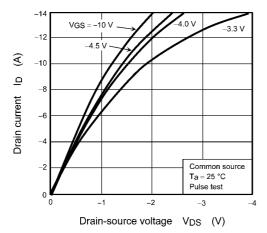


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

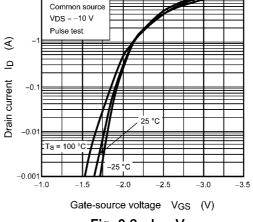


Fig. 8.2 I<sub>D</sub> - V<sub>GS</sub>

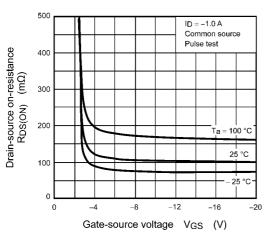


Fig. 8.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

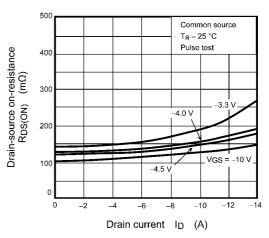


Fig. 8.4 R<sub>DS(ON)</sub> - I<sub>D</sub>

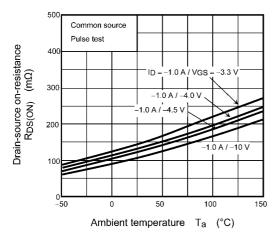


Fig. 8.5 R<sub>DS(ON)</sub> - T<sub>a</sub>

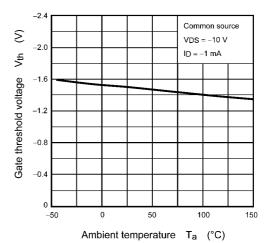


Fig. 8.6 V<sub>th</sub> - T<sub>a</sub>



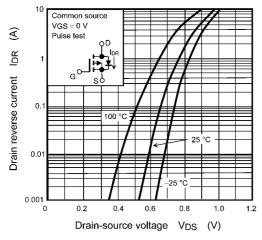


Fig. 8.7 IDR - VDS

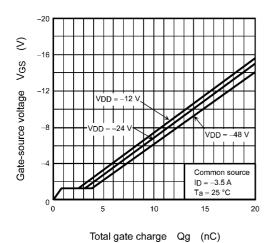


Fig. 8.9 Dynamic Input Characteristics

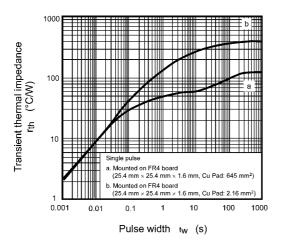


Fig. 8.11 rth - tw

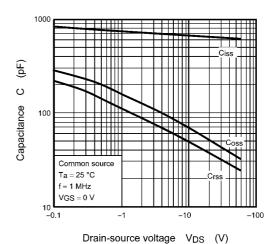


Fig. 8.8 C - V<sub>DS</sub>

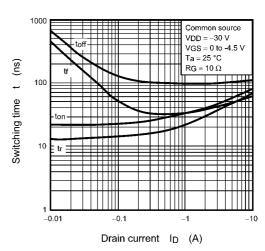


Fig. 8.10 t - I<sub>D</sub>

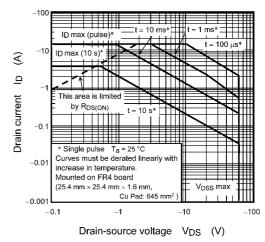


Fig. 8.12 Safe Operating Area



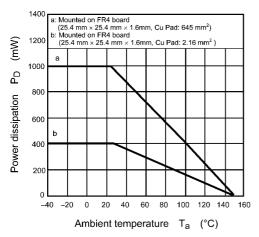


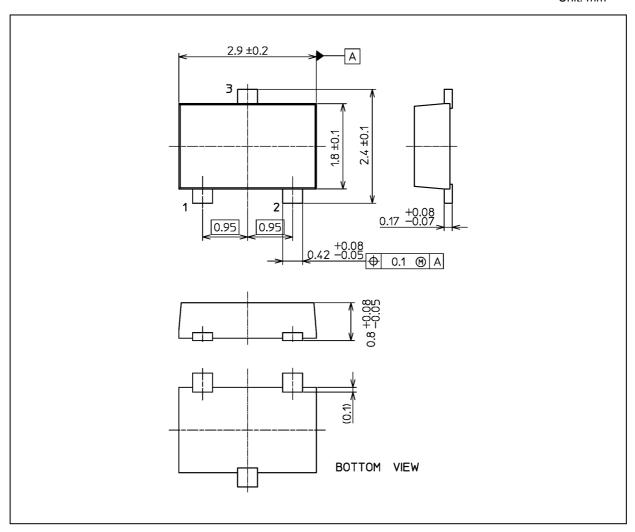
Fig. 8.13 P<sub>D</sub> - T<sub>a</sub>

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Weight: 0.011 g (typ.)

	Package Name(s)
Nickname: SOT-23F	



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